

## Donor–Acceptor-Stabilized Silicon Analogue of an Acid Anhydride

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**S** Supporting Information

**ABSTRACT:** A stable silicon analogue of an acid anhydride  $\{\text{PhC}(\text{Bu}^t\text{N})_2\}\text{Si}\{\text{=O}\cdot\text{B}(\text{C}_6\text{F}_5)_3\}\text{O}-\text{Si}(\text{H})\{\text{=O}\cdot\text{B}(\text{C}_6\text{F}_5)_3\}\{\text{(NBu}^t)(\text{HNBu}^t)\text{CPh}\}$  (**4**) with a  $\text{O}=\text{Si}-\text{O}-\text{Si}=\text{O}$  core has been prepared by treating monochlorosilylene  $\text{PhC}(\text{Bu}^t\text{N})_2\text{SiCl}$  (**1**) with  $\text{H}_2\text{O}\cdot\text{B}(\text{C}_6\text{F}_5)_3$  in the presence of NHC (NHC = 1,3-bis(2,6-diisopropylphenyl)imidazol-2-ylidene). Compound **4** has been characterized by elemental analysis and multinuclear NMR spectroscopic investigations. The molecular structure of **4** has been established by single-crystal X-ray diffraction studies, and DFT calculations support the experimental results.

The chemistry of compounds containing silicon–heteroatom multiple bonds has been one of the interesting areas of research in main group chemistry.<sup>1–6</sup> Compounds with formal double bonds to silicon ( $\text{Si}=\text{X}$ ) of group 16 elements ( $\text{X} = \text{O}, \text{S}, \text{Se}, \text{Te}$ ) are considered to be very reactive due to the highly polarized  $\text{Si}=\text{X}$  bond as well as weak  $p_\pi-p_\pi$  interactions. This behavior is more pronounced in compounds with a formal silicon–oxygen double bond ( $\text{Si}=\text{O}$ ) owing to oxygen having the highest electronegativity among the group 16 elements.

Nevertheless, some silicon compounds with  $\text{Si}=\text{X}$  double bond have been isolated<sup>3–12</sup> by taking advantage of kinetic and thermodynamic stabilization using specially designed ligands on silicon. The first successful attempt in this direction was made by Corriu et al.<sup>3</sup> with the isolation of base-stabilized silicon compounds containing  $\text{Si}=\text{S}$  and  $\text{Si}=\text{Se}$  bonds. Contributions to stabilize silicon compounds with  $\text{Si}=\text{X}$  bonds by the research groups of Wagler,<sup>4</sup> West,<sup>5</sup> Okazaki,<sup>6,7</sup> Tokitoh,<sup>6,7</sup> Kira,<sup>8</sup> and Driess<sup>9–12</sup> are noteworthy. Owing to the highly polarized nature of the  $\text{Si}=\text{O}$  bond, incorporation of a second substituent (OR, where  $\text{R} = \text{H}, \text{alkyl}, \text{or aryl}$ ) is a challenge.<sup>12,13</sup>

We have reported a base-stabilized silicon thioester analogue ( $\text{PhC}(\text{Bu}^t\text{N})_2\text{Si}(\text{=S})\text{SBu}^t$ ), **A** (Scheme 1).<sup>14</sup> Furthermore, base-stabilized germanium analogues of carboxylic acids  $\text{LGe}(\text{=X})\text{OH}$ , **B** ( $\text{X} = \text{S}, \text{Se}$ ; Scheme 1), supported by  $\beta$ -diketiminato ligand **L** ( $\text{L} = \text{CH}(\text{MeCNAr})_2$ ,  $\text{Ar} = 2,6\text{-Pr}^i_2\text{C}_6\text{H}_3$ ) were synthesized and completely characterized.<sup>15</sup> Silicon analogues of carboxylic acid  $\text{RSi}(\text{=O})\text{OH}$  are transient species and have been studied at low temperature in an argon matrix.<sup>16</sup> Driess and co-workers have explored the chemistry of silicon compounds<sup>9–12</sup> containing  $\text{Si}=\text{X}$  bonds that are stabilized by the  $\beta$ -diketiminato ligand. In a recent paper, they reported the isolation of the first silicon analogue of carboxylic acid  $\text{LSi}(\text{=O})\text{OH}$ , **C** (Scheme 1),

by donor–acceptor stabilization. A single-crystal X-ray structure analysis of **C** is still missing.<sup>12</sup>

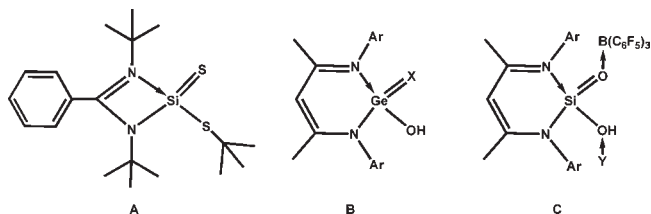
In contrast to silicon, related carbon compounds with  $\text{C}=\text{O}$  functionality are ubiquitous and well-known. An acid anhydride (**D**) is shown in Scheme 2. Compounds of this type exhibit important roles in many industrial processes. To the best of our knowledge, a silicon analogue (**E**) of an acid anhydride so far has not been reported. We have used N-heterocyclic carbenes (NHCs) as dehydrochlorinating agents for the preparation of dichlorosilylene,<sup>17</sup> germylene,<sup>18</sup> and metal hydroxides.<sup>19</sup> We successfully eliminated HCl from a silyl halide containing a secondary amino group using NHC to form an unstable compound with a  $\text{Si}=\text{N}$  double bond, which further dimerizes to a four-membered  $\text{Si}_2\text{N}_2$  ring.<sup>20</sup> In view of the above results, we became interested in preparing a compound with a  $\text{Si}=\text{O}$  bond starting from a chlorosilylene<sup>21</sup>  $\text{PhC}(\text{Bu}^t\text{N})_2\text{SiCl}$  (**1**) and  $\text{H}_2\text{O}\cdot\text{B}(\text{C}_6\text{F}_5)_3$  in the presence of NHC as a HCl scavenger.

Herein, we report on a silicon analogue of an acid anhydride  $\{\text{PhC}(\text{Bu}^t\text{N})_2\}\text{Si}\{\text{=O}\cdot\text{B}(\text{C}_6\text{F}_5)_3\}\text{O}-\text{Si}(\text{H})\{\text{=O}\cdot\text{B}(\text{C}_6\text{F}_5)_3\}\{\text{(NBu}^t)(\text{HNBu}^t)\text{CPh}\}$  (**4**; Scheme 3) containing the  $\text{O}=\text{Si}-\text{O}-\text{Si}=\text{O}$  moiety. Compound **4** was synthesized by treatment of a base-stabilized monochlorosilylene<sup>21</sup>  $\text{PhC}(\text{Bu}^t\text{N})_2\text{SiCl}$  (**1**) with  $\text{H}_2\text{O}\cdot\text{B}(\text{C}_6\text{F}_5)_3$  in the presence of NHC (NHC is  $\text{IPr} = 1,3\text{-bis}(2,6\text{-diisopropylphenyl})\text{imidazol-2-ylidene}$ ). The mechanism for the formation of **4** is not known; however we presume the involvement of a silaformaldehyde (**2b**) and a silacarboxylic acid (**3**) as depicted in Scheme 3. Formation of a monohydroxylsilylene  $\text{PhC}(\text{Bu}^t\text{N})_2\text{Si}(\text{HO}\cdot\text{B}(\text{C}_6\text{F}_5)_3)$  **2a** by the elimination of HCl as  $\text{IPr}\cdot\text{HCl}$  on reaction of **1** with  $\text{H}_2\text{O}\cdot\text{B}(\text{C}_6\text{F}_5)_3$  and its subsequent rearrangement to **2b** seems to be plausible.<sup>22</sup> Due to the high electronegativity of the oxygen atom and propensity of  $\text{Si}=\text{O}$  bonded compounds to exist as  $^+\text{Si}-\text{O}^-$ , **2b** can isomerize to **2c**. Cationic silicon in **2c** may abstract oxygen from  $\{\text{HOB}(\text{C}_6\text{F}_5)_3\}^-$ , formed by the reaction of  $\text{IPr}$  and  $\text{H}_2\text{O}\cdot\text{B}(\text{C}_6\text{F}_5)_3$ , with elimination of  $\{\text{HB}(\text{C}_6\text{F}_5)\}^-$  to result in silacarboxylic acid **3**. Protonation of the amino nitrogen of the amidinate ligand of **2b** by silacarboxylic acid **3** affords acid anhydride **4**. Compound **4** is a zwitterion in which anionic silacarboxylate oxygen coordinates to the second silicon atom that contains the protonated amidinate ligand. Compound **4** was isolated as colorless crystals and characterized by elemental analysis and NMR spectroscopy. The molecular structure of **4** was unequivocally established by single-crystal X-ray diffraction.

Received: July 25, 2011

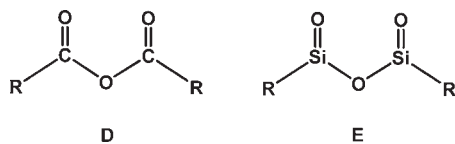
Published: October 14, 2011

**Scheme 1. Base-Stabilized Silicon or Germanium Analogues of Thioester (A), Thio- and Seleno-Carboxylic Acid (B; X = S or Se), and Carboxylic Acid (C)<sup>a</sup>**



<sup>a</sup> Ar = 2,6-Pr<sup>t</sup><sub>2</sub>C<sub>6</sub>H<sub>3</sub>, Y = 4-dimethylaminopyridine.

**Scheme 2. An Acid Anhydride (D) and Its Silicon Analogue (E)<sup>a</sup>**



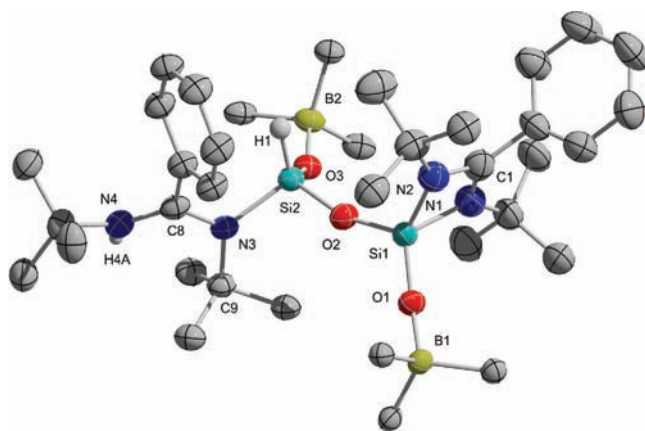
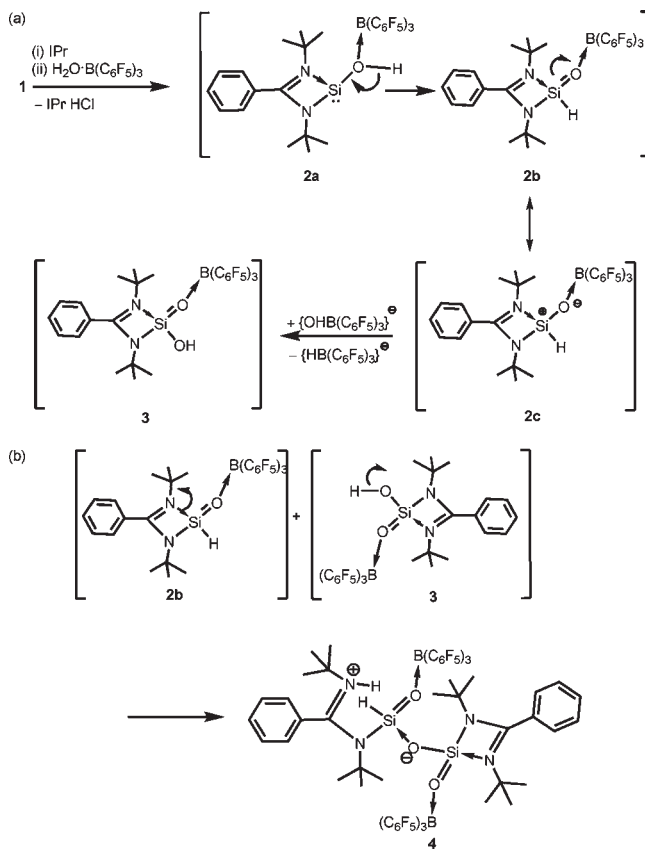
<sup>a</sup> R = alkyl or aryl group.

Compound **4** is stable under an inert atmosphere of nitrogen and soluble in common organic solvents. The <sup>1</sup>H NMR spectrum of **4** shows three sets of resonances for Bu<sup>t</sup> groups along with a complex multiplet for phenyl protons. A broad resonance at δ 10.27 ppm is tentatively assigned for the NH proton. The SiH proton appears as a broad resonance at δ 4.10 ppm.<sup>23</sup> The <sup>29</sup>Si{<sup>1</sup>H} NMR spectrum of **4** exhibits two resonances at δ -72.02 and -75.91 ppm. These resonances are consistent with those observed for compounds with a four-coordinate silicon atom.<sup>12</sup>

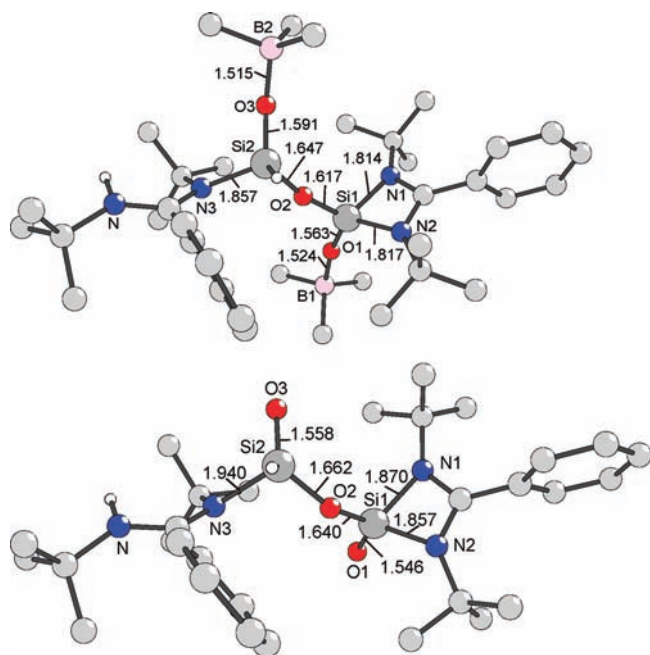
The molecular structure of compound **4** has been established by single-crystal X-ray diffraction and is shown in Figure 1. Compound **4** crystallizes as colorless crystals in the triclinic space group *P* $\bar{1}$ . The asymmetric unit contains one molecule of **4** and one and a half toluene molecules. Compound **4** features an interesting bonding situation and constitutes two functionalities within a single molecule. These are interpreted as a deprotonated silacarboxylic acid and silaldehyde moieties. Alternatively, two Si=O (silacarbonyl) groups are bridged by an oxygen atom, and therefore **4** represents the first silicon analogue of acid anhydride with an O=Si–O–Si=O core. Compound **4** is a zwitterionic species; this is characteristic for an amino acid.

Each of the silicon atoms in **4** is four-coordinate and centered at the distorted tetrahedron. One of the amidinate ligands chelates a silicon atom in a bidentate fashion with the N1–Si1–N2 bite angle of 72.09(13)°. Another amidinate ligand at the second silicon atom is arranged in a monodentate fashion, exhibiting a protonated amino group. Bonds to divalent silicon atom are expected to be longer in comparison to those of tetravalent silicon.<sup>24</sup> Therefore, the Si1–N1 (1.797(3) Å) and Si1–N2 (1.773(3) Å) bond lengths are slightly shorter than those found in compound **1**.<sup>21</sup> The silicon–oxygen bond lengths range from 1.5392(19) to 1.6272(19) Å and support the presence of an O=Si–O–Si=O core in **4**. They vary according to the electronic environment around the silicon atoms. The Si1–O1 bond length (1.5392(19) Å) is very close to the Si=O distance (1.545(2) Å) reported for

**Scheme 3. Synthesis of Silicon Analogue of Acid Anhydride 4 (IPr = 1,3-Bis(2,6-diisopropylphenyl)imidazol-2-ylidene): (a) Formation of Silaformaldehyde (2b) and Silacarboxylic Acid (3) as Intermediates; (b) Interaction of 2b and 3 Result in the Formation of 4**



**Figure 1.** ORTEP representation of molecular structure with displacement ellipsoids of **4**; anisotropic displacement parameters depicted at 50% probability. Only *ipso* carbon atoms of C<sub>6</sub>F<sub>5</sub> rings of B(C<sub>6</sub>F<sub>5</sub>)<sub>3</sub> and H atoms on Si2 and N4 are shown for clarity. Selected bond lengths [Å] and angles [deg]: Si1–O1 1.5392(19), Si2–O3 1.5804(18), Si1–O2 1.5829(19), Si2–O2 1.6272(19), Si1–N1 1.797(3), Si1–N2 1.773(3), Si1–N3 1.816(2), O1–B1 1.493(3), O3–B2 1.488(3); O1–Si–O2 115.12(10), Si1–O2–Si2 163.20(14), O2–Si2–O3 112.08(10), O1–Si1–N1 114.28(12), N1–Si1–O2 112.78(12), O2–Si2–N3 106.00(10), N1–Si1–N2 72.09(13).



**Figure 2.** Calculated geometries (BP86/TZVPP-SVP) of **4** (top) and **4M** (bottom). Selected bond lengths are given in Å.

the compound with a four-coordinate silicon atom.<sup>11c</sup> The Si2–O2 bond length (1.6272(19) Å) is consistent with the Si–O single bond.<sup>12</sup> The Si2–O3 (1.5804(18) Å) and Si1–O2 (1.5829(19) Å) bond lengths are shorter than the Si–O single bond but longer than the Si=O double bond distances. Slight elongation of Si2–O3 and shortening of Si1–O2 bond lengths may be due to steric hindrance or to the electronic interaction of the Lewis acid B(C<sub>6</sub>F<sub>5</sub>)<sub>3</sub>.<sup>12</sup> The Si1–O2–Si2 (163.20(14)°) bond features the largest bond angle.

We carried out DFT calculations at the BP86/TZVPP-SVP level (see Supporting Information) for compound **4** and the uncomplexed parent system **4M** without the B(C<sub>6</sub>F<sub>5</sub>)<sub>3</sub> molecules. Figure 2 shows the optimized geometries of **4** and **4M**. The calculated bond lengths of **4** are in good agreement with those of the experiment. The computed Si–O distances are 0.01–0.03 Å longer than the X-ray values. The calculated Si1–O1 bond length (1.563 Å) is shorter than the Si2–O3 distance (1.591 Å), while the Si1–O2 (1.617 Å) and Si2–O2 bonds (1.647 Å) are still longer, which concurs with the experiment. The complexation of **4** with two B(C<sub>6</sub>F<sub>5</sub>)<sub>3</sub> molecules at the terminal oxygen atoms complicates the assignment of the Si–O linkages as single or double bonds. The calculated bond lengths of **4M** give a much clearer picture of the bonding situation. The terminal Si1–O1 (1.546 Å) and Si2–O3 bonds (1.558 Å) are much shorter than the bridging Si1–O2 (1.640 Å) and Si2–O2 bonds (1.662 Å). The former distances agree with the classification of double bonds, while the latter values concur with typical Si–O single bonds. Complexation of **4** with B(C<sub>6</sub>F<sub>5</sub>)<sub>3</sub> molecules at the terminal oxygen atoms lengthens the Si1–O1 and Si2–O3 bonds, and it shortens the Si1–O2 and Si2–O2 bonds.

Moreover, we analyzed the nature of the Si=O bond in **4** and in **4M** with the NBO method. The  $\pi$ -bond in **4** is strongly polarized toward the oxygen end. The NBO data suggest that 91.7% of the Si=O  $\pi$  bond is at oxygen, while only 8.3% is at silicon. The most appropriate Lewis structure for **4** should thus be written with a negative partial charge at O(–) and a positive

charge at Si(+). The nature of the  $\pi$  bond changes very little after complexation with the Lewis acid at oxygen. The Si=O  $\pi$  bond in **4M** is a bit more polarized toward oxygen (95.5%), while only 4.5% is at silicon. It follows that the Si=O bonding situations in **4** and in **4M** are very similar.

In summary, we report here for the first time a stable silicon analogue of an acid anhydride {PhC(Bu<sup>t</sup>N)<sub>2</sub>}Si{=O·B(C<sub>6</sub>F<sub>5</sub>)<sub>3</sub>}–O–Si(H){=O·B(C<sub>6</sub>F<sub>5</sub>)<sub>3</sub>}{(NBu<sup>t</sup>)(HNBu<sup>t</sup>)CPh} (**4**). Compound **4** was prepared by the reaction of monochlorosilylene PhC(Bu<sup>t</sup>N)<sub>2</sub>SiCl (**1**) with the water–borane adduct H<sub>2</sub>O·B(C<sub>6</sub>F<sub>5</sub>)<sub>3</sub> in the presence of NHC. NHC serves as a HCl scavenger. Compound **4** was characterized by elemental analysis and multinuclear NMR spectroscopic investigations. The molecular structure of **4** was established by single-crystal X-ray diffraction study. DFT calculations support the experimental results.

## ■ ASSOCIATED CONTENT

**S Supporting Information.** Experimental procedures and X-ray crystallographic and computational information of compound **4**. This material is available free of charge via the Internet at <http://pubs.acs.org>.

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## ■ ACKNOWLEDGMENT

Support of the *Deutsche Forschungsgemeinschaft* is highly acknowledged. R. A. is thankful to AvHS for a fellowship. This paper is dedicated to Professor Karl Otto Christe.

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(22) All manipulations were carried out in strictly anhydrous and oxygen-free atmosphere using glovebox or Schlenk-line techniques. Reaction of **1** with H<sub>2</sub>O results in the formation of amidinate salt PhC(Bu<sup>t</sup>NH)<sub>2</sub>·HCl with no silicon in the toluene-soluble part, most probably due to the formation of (SiO<sub>2</sub>).

(23) Due to rapid hydrogen exchange on the NMR time scale even at low-temperature, it was not possible to measure <sup>29</sup>Si–<sup>1</sup>H coupling. Therefore, <sup>29</sup>Si NMR resonances for both silicon atoms in **4** appear almost in the same region.

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